

Product Summary

$V_{(BR)DSS}$	Max $R_{DS(on)}$	I_D Max (Note 5) $T_A = 25^\circ\text{C}$
30V	460m Ω @ $V_{GS} = 4.5\text{V}$	0.94A
	560m Ω @ $V_{GS} = 2.5\text{V}$	0.85A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

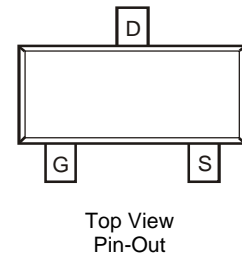
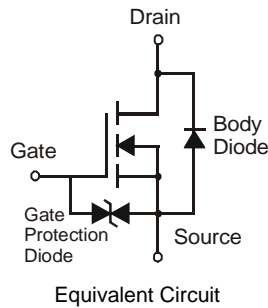
- Load switch
- Portable applications
- Power Management Functions

Features and Benefits

- Low $V_{GS(th)}$, can be driven directly from a battery
- Low $R_{DS(on)}$
- “Lead Free”, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- ESD Protected Gate 2kV
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin.
- Weight: 0.08 grams (approximate)

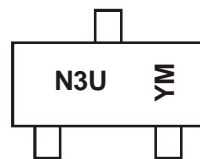


Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3730U-7	N3U	7	8	3,000

Notes: 1. No purposefully added lead

Marking Information



N3U = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: Y = 2011)
M = Month (ex: 9 = September)

Date Code Key

Year Code	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current	Steady State	$T_A = 25^\circ\text{C}$ (Note 5)	I_D	0.94	A
		$T_A = 85^\circ\text{C}$ (Note 5)		0.68	
		$T_A = 25^\circ\text{C}$ (Note 4)		0.75	
Pulsed Drain Current (Note 6)			I_{DM}	10	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	P_D	0.45	W
	(Note 5)		0.71	W
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	275	$^\circ\text{C/W}$
	(Note 5)		177	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
2. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
 3. Device mounted on 25mm X 25mm square copper plate with FR-4 substrate PC board, 2oz copper
 4. Device mounted on minimum recommended pad layout test board, 10 μs pulse duty cycle = 1%.

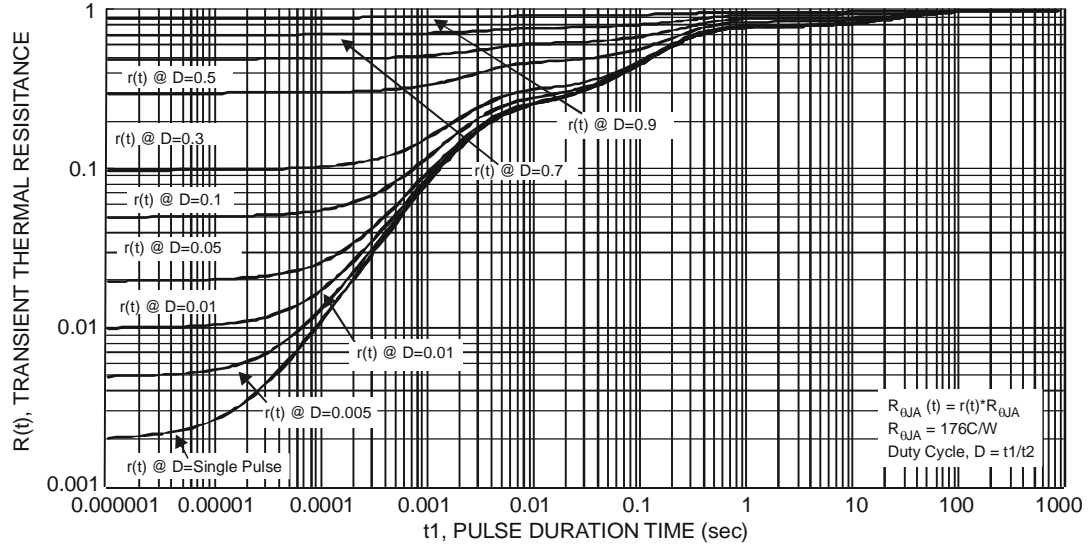


Fig. 3 Transient Thermal Resistance

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	3	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	0.45	-	0.95	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(on)}$	-	-	460	$m\Omega$	$V_{GS} = 4.5V, I_D = 200mA$
				560		$V_{GS} = 2.5V, I_D = 100mA$
				730		$V_{GS} = 1.8V, I_D = 75mA$
Forward Transfer Admittance	$ Y_{fs} $	40	-	-	mS	$V_{DS} = 3V, I_D = 10mA$
Diode Forward Voltage (Note 7)	V_{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_S = 300mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	64.3	-	pF	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	6.1	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	4.5	-	pF	
Gate Resistance	R_g	-	70	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	-	1.6	-	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_D = 1A$
Gate-Source Charge	Q_{gs}	-	0.2	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.2	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	3.5	-	ns	$V_{DS} = 10V, I_D = 1A$ $V_{GS} = 10V, R_G = 6\Omega$
Turn-On Rise Time	t_r	-	2.8	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	38	-	ns	
Turn-Off Fall Time	t_f	-	13	-	ns	

Notes: 5. Measured under pulsed conditions to minimize self-heating effect. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$
6. For design aid only, not subject to production testing.